### Refine Search

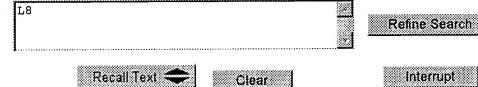


#### Search Results -

Terms	Documents	
L5 and fluorocarbon	1	

US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
US OCR Full-Text Database
US OCR Full-Text Database
EPO Abstracts Database
JPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

Search:



# Search History

DATE: Sunday, March 21, 2004 Printable Copy Create Case

Set Name side by side	Query	Hit Count	<u>Set</u> <u>Name</u> result set
DB=U	SPT; PLUR=YES; OP=ADJ		
<u>L8</u>	L5 and fluorocarbon	1	<u>L8</u>
<u>L7</u>	L5 and (deoxidizing or deoxidize or deoxidation)	0	<u>L7</u>
<u>L6</u>	L5 and deoxidizing or deoxidize or deoxidation	2596	<u>L6</u>
<u>L5</u>	L4 and (silicon adj oxide) and (silicon adj nitride) and patterning and trench	10	<u>L5</u>
<u>L4</u>	antireflection and reduction and hydrogen and thermal	269	<u>L4</u>
<u>L3</u>	antireflection and (deoxidize or deoxidizing) and hydrogen and thermal	0	<u>L3</u>
<u>L2</u>	deoxidiz? near7 (antireflection) <sup>t</sup>	0	<u>L2</u>
<u>L1</u>	deoxidizing near4 (antireflection)	0	<u>L1</u>

#### **END OF SEARCH HISTORY**

### **Hit List**

Clear Generate Collection Print Fwd Refs Bkwd Refs
Generate OACS

Search Results - Record(s) 1 through 10 of 10 returned.

1. Document ID: US 6686236 B2

L5: Entry 1 of 10

File: USPT

Feb 3, 2004

US-PAT-NO: 6686236

DOCUMENT-IDENTIFIER: US 6686236 B2

TITLE: Methods of preventing <u>reduction</u> of IrOx during PZT formation by metalorganic chemical vapor deposition or other processing

Full Title Citation Front Review Classification Date Reference Claims KMC Draw D.

2. Document ID: US 6635497 B2

L5: Entry 2 of 10

File: USPT

Oct 21, 2003

US-PAT-NO: 6635497

DOCUMENT-IDENTIFIER: US 6635497 B2

TITLE: Methods of preventing reduction of IrOx during PZT formation by metalorganic

chemical vapor deposition or other processing

Full Title Citation Front Review Classification Date Reference Communication Date Reference Communication Claims Wild Draw Da

3. Document ID: US 6596547 B2

L5: Entry 3 of 10

File: USPT

Jul 22, 2003

US-PAT-NO: 6596547

DOCUMENT-IDENTIFIER: US 6596547 B2

TITLE: Methods of preventing <u>reduction</u> of IrOx during PZT formation by metalorganic chemical vapor deposition or other processing

Full Title Citation Front Review Classification Date Reference Communication Claims Could Dispus Dis-

4. Document ID: US 6528386 B1

L5: Entry 4 of 10

File: USPT

Mar 4, 2003

Page 2 of 3 Record List Display

US-PAT-NO: 6528386

DOCUMENT-IDENTIFIER: US 6528386 B1

TITLE: Protection of tungsten alignment mark for FeRAM processing

Full Title Citation Front Review Classification Date Reference Claims (AVIC Draw) Oc 5. Document ID: US 6528328 B1

L5: Entry 5 of 10

File: USPT

Mar 4, 2003

Dec 31, 2002

US-PAT-NO: 6528328

DOCUMENT-IDENTIFIER: US 6528328 B1

TITLE: Methods of preventing <a href="reduction">reduction</a> of irox during PZT formation by metalorganic chemical vapor deposition or other processing

Full Title Citation Front Review Classification Date Reference Claims KWC Draw D. 6. Document ID: US 6500678 B1

File: USPT

US-PAT-NO: 6500678

L5: Entry 6 of 10

DOCUMENT-IDENTIFIER: US 6500678 B1

TITLE: Methods of preventing reduction of IrOx during PZT formation by metalorganic

chemical vapor deposition or other processing

Full Title Citation Front Review Classification Date Reference Claims KiMC Draw De 7. Document ID: US 6498089 B2

L5: Entry 7 of 10

File: USPT

Dec 24, 2002

US-PAT-NO: 6498089

DOCUMENT-IDENTIFIER: US 6498089 B2

TITLE: Semiconductor integrated circuit device with moisture-proof ring and its

manufacture method

Full Title Citation Front Review Classification Date Reference Claims RMC Draws Do

8. Document ID: US 6492222 B1

L5: Entry 8 of 10

File: USPT

Dec 10, 2002

US-PAT-NO: 6492222

DOCUMENT-IDENTIFIER: US 6492222 B1

Record List Display Page 3 of 3

TITLE: Method of dry etching PZT capacitor stack to form high-density ferroelectric memory devices

9. Document ID: US 6365512 B1
L5: Entry 9 of 10

File: USPT

Apr 2, 2002

US-PAT-NO: 6365512

DOCUMENT-IDENTIFIER: US 6365512 B1

TITLE: Method and apparatus for a direct buried strap for same level contact

interconnections for semiconductor devices

Full Title Chailon Front Review Classification Date Retainers Claims RWC Draw Do

US-PAT-NO: 6303483

DOCUMENT-IDENTIFIER: US 6303483 B1

TITLE: Method of manufacturing semiconductor device

Full Title Citation Front Review Classification Date Reference	Claims RMC Draw Dr
Clear Generate Collection Print Fwd Refs Bkv	d Refs Generate OACS
Terms	Documents
L4 and (silicon adj oxide) and (silicon adj nitride) and patter trench	rning and 10

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Previous Page Next Page Go to Doc#

Page 1 of 1 Record List Display

# **Hit List**

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# Search Results - Record(s) 1 through 1 of 1 returned.

1. Document ID: US 6492222 B1

L8: Entry 1 of 1 File: USPT Dec 10, 2002

US-PAT-NO: 6492222

DOCUMENT-IDENTIFIER: US 6492222 B1

TITLE: Method of dry etching PZT capacitor stack to form high-density ferroelectric

memory devices

Full Title Citation Front Review Classification Date	3 Reference Claims AMC Draw
	Fwd Refs Bkwd Refs Generate OACS
Terms	Documents
L5 and fluorocarbon	1

Change Format Display Format: TI

Previous Page Next Page Go to Doc#